TOSHIBA 3JU41

TOSHIBA RECTIFIER SILICON DIFFUSED TYPE

3 J U 4 1

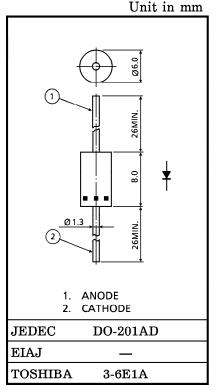
HIGH SPEED RECTIFIER APPLICATIONS (FAST RECOVERY)

 $\begin{array}{lll} \bullet & \text{Average Forward Current} & : I_{F\,(AV)} \! = \! 3.0V \\ \bullet & \text{Repetitive Peak Reverse Voltage} & : V_{RRM} \! = \! 600V \\ \bullet & \text{Reverse Recovery Time} & : t_{rr} \! = \! 100 \text{ns (Max.)} \\ \end{array}$

• Plastic Mold Type.

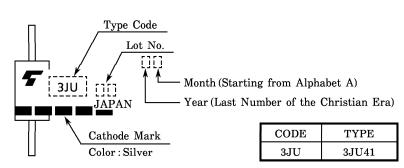
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	v_{RRM}	600	V	
Average Forward Current	I _{F (AV)}	3.0	Α	
Peak One Cycle Surge Forward	Traces	50 (50Hz)	A	
Current (Non-Repetitive)	I_{FSM}	55 (60Hz)		
Junction Temperature	Tj	-40~150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$T_{ m stg}$	-40~150	°C	



Weight: 1.18g

Marking



961001EAA2

[■] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

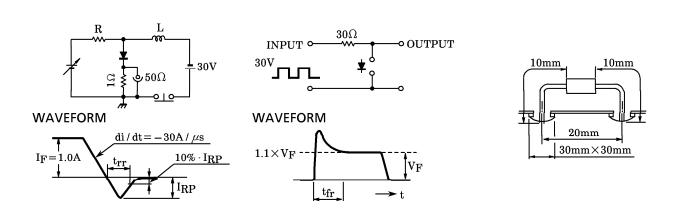
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	${ m v_{FM}}$	$I_{\text{FM}} = 3.0 \text{A}$	_		2.0	V
Repetitive Peak Reverse Current	${ m I}_{ m RRM}$	$V_{ m RRM}$ =600 V	_	_	100	μ A
Reverse Recovery Time (Note 1)	$ m t_{rr}$	$I_F=1A$, di/dt=-30A/ μ s	_	_	100	ns
Forward Recovery Time (Note 2)	t_{fr}	$I_{ m F}$ = 1.0A	_	_	250	ns
Thermal Resistance (Note 3)	R _{th (j-a)}	Junction to Ambient	_	_	41	°C/W
Thermal Resistance (Note 3)	$\mathrm{R}_{\mathrm{th}(\mathrm{j-}\ell)}$	Junction to Lead	_	_	7	°C/W

Note $1:t_{rr}$ TEST CIRCUIT

Note 2: tfr TEST CIRCUIT

Note 3: THERMAL RESISTANCE



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